

74AUP1G126

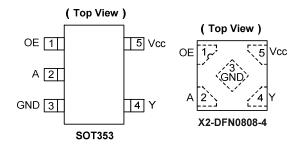
SINGLE BUFFER GATE WITH 3-STATE OUTPUT

Description

The Advanced, Ultra Low Power (AUP) CMOS logic family is designed for low power and extended battery life in portable applications.

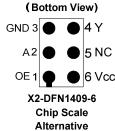
The 74AUP1G126 is a single, non-inverting, buffer/bus driver, designed for operation over a power supply range of 0.8V to 3.6V. The device has a three-state output that enters a high-impedance state when a LOW-level is applied to the Output Enable (OE) pin. The device is fully specified for partial power down applications using $l_{\rm OFF}$. The $l_{\rm OFF}$ circuitry disables the output, preventing damaging current backflow when the device is powered down.

Pin Assignments











Packages not to scale

Features

- Advanced Ultra Low Power (AUP) CMOS
- Supply Voltage Range from 0.8V to 3.6V
- ±4mA Output Drive at 3.0V
- Low Static Power Consumption

 $I_{CC} < 0.9 \mu A$

• Low Dynamic Power Consumption

 $C_{PD} = 6.3pF$ (Typical at 3.6V)

- Schmitt Trigger Action at all inputs makes the circuit tolerant for slower input rise and fall time. The hysteresis is typically 250mV at V_{CC} = 3.0V.
- I_{OFF} Supports Partial-Power-Down Mode Operation
- ESD Protection Exceeds JESD 22

2000-V Human Body Model (A114)

Exceeds 1000-V Charged Device Model (C101)

- Latch-Up Exceeds 100mA per JESD 78, Class I
- Leadless Packages named per JESD30E
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

Applications

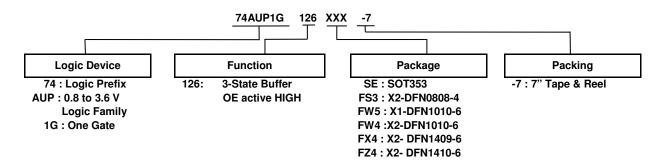
- Suited for Battery and Low Power Needs
- · Wide array of products such as:
 - Tablets, E-readers
 - Cell Phones, Personal Navigation / GPS
 - MP3 Players ,Cameras, Video Recorders
 - PCs, Ultrabooks, Notebooks, Netbooks,
 - Computer Peripherals, Hard Drives, CD/DVD ROMs
 - TVs, DVDs, DVRs, Set-Top Boxes

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 - 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.



Ordering Information



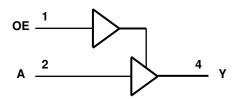
Device	Package	Package	Package	7" Tape	and Reel
Device	Code	(Notes 4 & 5)	Size	Quantity	Part Number Suffix
74AUP1G126SE-7	SE	SOT353	2.0mm x 2.0mm x 1.1mm 0.65 mm lead pitch	3,000/Tape & Reel	-7
74AUP1G126FS3-7	FS3	X2-DFN0808-4	0.8mm x 0.8mm x 0.35mm 0.5 mm pad pitch (diamond)	5,000/Tape & Reel	-7
74AUP1G126FW5-7	FW5	X1-DFN1010-6	1.0mm x 1.0mm x 0.5mm 0.35 mm pad pitch	5,000/Tape & Reel	-7
74AUP1G126FW4-7	FW4	X2-DFN1010-6	1.0mm x 1.0mm x 0.4mm 0.35 mm pad pitch	5,000/Tape & Reel	-7
74AUP1G126FX4-7	FX4	X2-DFN1409-6 Chip Scale Alternative	1.4mm x 0.9mm x 0.4mm 0.5 mm pad pitch	5,000/Tape & Reel	-7
74AUP1G126FZ4-7	FZ4	X2-DFN1410-6	1.4mm x 1.0mm x 0.4mm 0.5 mm pad pitch	5,000/Tape & Reel	-7

Notes: 4. Pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.

Pin Descriptions

Pin Name	Function
OE	Output Enable
Α	Data Input
GND	Ground
Y	Data Output
Vcc	Supply Voltage

Logic Diagram



Function Table

Inp	Inputs						
OE	Α	Υ					
Н	Н	Н					
Н	L	L					
L	X	Z					

^{5.} The taping orientation is located on our website at http://www.diodes.com/datasheets/ap02007.pdf.



Absolute Maximum Ratings (Notes 6 & 7) (@T_A = +25 °C, unless otherwise specified.)

Symbol	Description	Rating	Unit
ESD HBM	Human Body Model ESD Protection	2	kV
ESD CDM	Charged Device Model ESD Protection	1	kV
V _{CC}	Supply Voltage Range	-0.5 to +4.6	V
VI	Input Voltage Range	-0.5 to +4.6	V
Vo	Voltage Applied to Output in High or Low State	-0.5 to V _{CC} +0.5	V
I _{IK}	Input Clamp Current V _I < 0	50	mA
lok	Output Clamp Current (V _O < 0)	50	mA
lo	Continuous Output Current (V _O = 0 to V _{CC})	±20	mA
lcc	Continuous Current Through V _{CC}	50	mA
I _{GND}	Continuous Current Through GND	-50	mA
TJ	Operating Junction Temperature	-40 to +150	℃
T _{STG}	Storage Temperature	-65 to +150	℃

Notes:

Recommended Operating Conditions (Note 8) (@T_A = +25 ℃, unless otherwise specified.)

Symbol	Para	ameter	Min	Max	Unit
V _{CC}	Operating Voltage		0.8	3.6	V
V_{I}	Input Voltage		0	3.6	V
Vo	Output Voltage		0	V _{CC}	V
	I _{OH} High-Level Output Current	$V_{CC} = 0.8V$	_	-20	μΑ
		$V_{CC} = 1.1V$	_	-1.1	
		$V_{CC} = 1.4V$	_	-1.7	
ЮН		V _{CC} = 1.65V	_	-1.9	mA
		V _{CC} = 2.3V	_	-3.1	
		$V_{CC} = 3.0V$	_	-4	
		$V_{CC} = 0.8V$	_	20	μΑ
		V _{CC} = 1.1V	_	1.1	
	Lavel aval Output Commant	V _{CC} = 1.4V	_	1.7	
loL	Low-Level Output Current	V _{CC} = 1.65V	_	1.9	mA
		$V_{CC} = 2.3V$	_	3.1	
		V _{CC} = 3.0V	_	4	
Δt/ΔV	Input Transition Rise or Fall Rate	V _{CC} = 0.8V to 3.6V	_	200	ns/V
T _A	Operating Free-Air Temperature		-40	+125	.€

Note:

8. Unused inputs should be held at VCC or Ground.

^{6.} Stresses beyond the absolute maximum may result in immediate failure or reduced reliability. These are stress values and device operation should be within recommend values.

^{7.} Forcing the maximum allowed voltage could cause a condition exceeding the maximum current or conversely forcing the maximum current could cause a condition exceeding the maximum voltage. The ratings of both current and voltage must be maintained within the controlled range.



Electrical Characteristics (@ $T_A = +25$ °C, unless otherwise specified.)

Cumabal	Davamatav	Took Conditions	.,	T _A = +	25℃	T _A = -40°C	C to +85℃	Unit	
Symbol	Parameter	Test Conditions	V _{CC}	Min	Max	Min	Max		
		_	0.8V to 1.65V	0.80 x V _{CC}	_	0.80 x V _{CC}	_		
V _{IH}	High-Level Input	_	1.65V to 1.95V	0.65 x V _{CC}	_	0.65 x V _{CC}	_	V	
VIH	Voltage	_	2.3V to 2.7V	1.6	_	1.6	_	v	
		_	3.0V to 3.6V	2.0	_	2.0	_		
		_	0.8V to 1.65V	_	0.30 x V _{CC}	_	0.30 x V _{CC}		
VIL	Low-Level Input	_	1.65V to 1.95V	_	0.35 x V _{CC}	_	0.35 x V _{CC}	V	
VIL	Voltage	_	2.3V to 2.7V	_	0.7	_	0.7	v	
		_	3.0V to 3.6V	_	0.9	_	0.9		
		$I_{OH} = -20\mu A$	0.8V to 3.6V	V _{CC} - 0.1	_	V _{CC} - 0.1	_		
		I _{OH} = -1.1mA	1.1V	0.75 x V _{CC}	_	0.7 x V _{CC}	_		
		I _{OH} = -1.7mA	1.4V	1.11	_	1.03	_		
V	High-Level Output	I _{OH} = -1.9mA	1.65V	1.32	_	1.3	_	V	
V_{OH}	Voltage	I _{OH} = -2.3mA	0.01/	2.05	_	1.97	_	v	
		I _{OH} = -3.1mA	2.3V	1.9	_	1.85	_		
		I _{OH} = -2.7mA	01/	2.72	_	2.67	_		
		I _{OH} = -4mA	3V	2.6	_	2.55	_		
		I _{OL} = 20μA	0.8V to 3.6V	_	0.1	_	0.1		
		I _{OL} = 1.1mA	1.1V	_	0.3 x V _{CC}	_	0.3 x V _{CC}		
		I _{OL} = 1.7mA	1.4V	_	0.31	_	0.37		
	Low-Level Output	I _{OL} = 1.9mA	1.65V	_	0.31	_	0.35	١.,	
V_{OL}	Voltage	I _{OL} = 2.3mA		_	0.31	_	0.33	V	
		I _{OL} = 3.1mA	2.3V	_	0.44	_	0.45		
		I _{OL} = 2.7mA		_	0.31	_	0.33		
		I _{OL} = 4mA	3V	_	0.44	_	0.45		
lı	Input Current	A or B Input V _I = GND to 3.6V	0 to 3.6V	_	±0.1	_	±0.5	μA	
loff	Power Down Leakage Current	V_I or $V_O = 0V$ to 3.6V	0	_	±0.2	_	±0.5	μA	
loz	Z State Leakage Current	V _O = 3.6V V _i = 3.6V	3.6V	_	±0.2	_	±0.5	μΑ	
Δl _{OFF}	Delta Power Down Leakage Current	V_1 or $V_0 = 0V$ to 3.6V	0 to 0.2V	_	0.2	_	0.6	μΑ	
Icc	Supply Current	$V_I = GND \text{ or } V_{CC}, I_O = 0$	0.8V to 3.6V	_	0.5	_	0.9	μA	
		Data Input at V _{CC} -0.6V OE = GND I _O = 0A	3.3V	_	40	_	50	μΑ	
ΔI _{CC}	Additional Supply	OE Input at V _{CC} -0.6V Data Input = GND or V _{CC} , I _O = 0A	3.3V	_	110	_	120	μΑ	
		OE Input at GND Data Input = GND to 3.6V, I _O = 0A	0.8V to 3.6V	_	1	_	1	μΑ	



Electrical Characteristics (continued) (@T_A = +25 °C, unless otherwise specified.)

		T 10 I''	.,	T _A = -40 ℃	to +125℃	
Symbol	Parameter	Test Conditions	V _{CC}	Min	Max	Unit
		_	0.8V to 1.65V	0.80 x V _{CC}	_	
VIH	High-Level Input	_	1.65V to 1.95V	0.70 x V _{CC}	_	V
VIH	Voltage	_	2.3V to 2.7V	1.6	_	V
		_	3.0V to 3.6V	2.0	_	
		_	0.8V to 1.65V	_	0.25 x V _{CC}	
V _{IL}	Low-Level Input	_	1.65V to 1.95V	_	0.35 x V _{CC}	V
VIL	Voltage	_	2.3V to 2.7V	_	0.7	v
		_	3.0V to 3.6V		0.9	
		$I_{OH} = -20\mu A$	0.8V to 3.6V	V _{CC} – 0.11	_	
		I _{OH} = -1.1mA	1.1V	0.6 x V _{CC}	_	
		$I_{OH} = -1.7 \text{mA}$	1.4V	0.93	_	
V	High-Level Output	I _{OH} = -1.9mA	1.65V	1.17	_	V
V _{OH}	Voltage	I _{OH} = -2.3mA	0.01/	1.77	_	v
		I _{OH} = -3.1mA	2.3V	1.67	_	
		I _{OH} = -2.7mA	0)/	2.40	_	
		I _{OH} = -4mA	3V	2.30	_	
		I _{OL} = 20μA	0.8V to 3.6V	_	0.11	
		I _{OL} = 1.1mA	1.1V	_	0.3 x V _{CC}	
		I _{OL} = 1.7mA	1.4V	_	0.41	
	Low-Level Output	I _{OL} = 1.9mA	1.65V	1.65V — 0.3		.,
V_{OL}	Voltage	I _{OL} = 2.3mA	2.01/	_	0.36	V
		I _{OL} = 3.1mA	2.3V	_	0.50	
		I _{OL} = 2.7mA		_	0.36	
		I _{OL} = 4mA	3V	_	0.50	
lı	Input Current	A or B Input V _I = GND to 3.6V	0 to 3.6V	_	±0.75	μA
loff	Power Down Leakage Current	V _I or V _O = 0V to 3.6V	0	_	±3.5	μA
loz	Z State Leakage Current	V _O = 3.6V V _i = 3.6V	3.6V	_	±1.5	μΑ
Δl _{OFF}	Delta Power Down Leakage Current	V_I or $V_O = 0V$ to 3.6V	0V to 0.2V	_	±2.5	μΑ
Icc	Supply Current	$V_I = GND \text{ or } V_{CC}, I_O = 0$	0.8V to 3.6V	_	3.0	μΑ
		Data Input at V _{CC} -0.6V OE = GND I _O = 0A	3.3V	_	75	μΑ
ΔI _{CC}	Additional Supply	OE input at V _{CC} -0.6V Data Input = GND or V _{CC} , I _O = 0A	3.3V	_	180	μΑ
		OE Input at GND Data Input = GND to 3.6V, I _O = 0A	0.8V to 3.6V	_	1	μΑ



Switching Characteristics

C_L = 5pF, See Figure 1

Parameter	From	То	Vaa	T	A = +25°	С	T _A = -40 °C	C to +85℃	T _A = -40 °C to +125 °C		Unit
Parameter	Input	Output	V _{CC}	Min	Тур	Max	Min	Max	Min	Max	Ullit
			V8.0	_	20.6	_	_	_	_	_	
			1.2V ± 0.1V	2.5	5.5	10.5	2.5	11.7	2.5	12.9	
	Α	Y	1.5V ± 0.1V	2.0	3.9	6.1	2.0	7.3	2.0	8.1	
t _{pd}	A	Ť	1.8V ± 0.15V	1.9	3.2	4.8	1.7	6.1	1.7	6.7	ns
			2.5V ± 0.2V	1.6	2.6	3.6	1.4	4.3	1.4	4.9	
			3.3V ± 0.3V	1.4	2.4	3.1	1.2	3.9	1.2	4.4	
			V8.0	_	71.6	_	_	_	_	_	ns
	OE	Y	1.2V ± 0.1V	2.8	6.2	12.4	2.6	13.6	2.6	13.6	
			1.5V ± 0.1V	2.1	4.2	6.9	2.1	7.4	2.1	7.7	
t _{en}	OE		1.8V ± 0.15V	1.7	3.3	5.3	1.7	5.9	1.7	6.2	
			2.5V ± 0.2V	1.4	2.4	3.6	1.4	3.8	1.4	4.1	
			3.3V ± 0.3V	1.3	2.0	2.9	1.2	3.2	1.2	3.4	
			V8.0	_	10.3	_	_	_	_	_	
			1.2V ± 0.1V	2.6	4.2	8.2	2.6	8.9	2.6	8.9	
	OΓ	Y	1.5V ± 0.1V	2.1	3.2	6.7	2.1	7.0	2.1	7.0	
t _{dis}	OE	Y	1.8V ± 0.15V	1.7	3.1	6.2	1.7	6.5	1.7	6.5	ns ns
		_	2.5V ± 0.2V	1.3	2.9	5.7	1.3	5.8	1.3	5.8	
			3.3V ± 0.3V	1.2	2.8	4.5	1.2	4.7	1.2	4.7	

 $C_L = 10pF$, See Figure 1

Dougnator	From	То	V	T	_A = +25°	С	T _A = -40 ℃	C to +85℃	T _A = -40 ℃	to +125℃	Unit
Parameter	Input	Output	V _{CC}	Min	Тур	Max	Min	Max	Min	Max	Unit
			0.8V	_	24.0	_	_	_	_	_	
			1.2V ± 0.1V	2.6	6.4	12.3	2.6	13.8	2.6	15.2	
	Α	Y	1.5V ± 0.1V	2.1	4.5	7.3	2.1	8.5	2.1	9.4	no
t _{pd}	A	ī	1.8V ± 0.15V	1.9	3.8	5.5	1.9	6.8	1.9	7.6	ns
			2.5V ± 0.2V	1.7	3.2	4.2	1.7	5.3	1.7	5.9	
			3.3V ± 0.3V	1.6	3.0	3.8	1.6	4.6	1.6	5.2	
	OE	Y	0.8V	_	75.3	_	_	_	_	_	ns
			1.2V ± 0.1V	3.0	7.1	14.1	3.0	15.4	3.0	15.4	
			1.5V ± 0.1V	2.1	4.8	8.0	2.1	8.3	2.1	8.6	
t _{en}	OE		1.8V ± 0.15V	1.7	3.9	5.9	1.7	6.5	1.7	6.8	
			2.5V ± 0.2V	1.4	2.9	4.2	1.4	4.5	1.4	4.8	
			3.3V ± 0.3V	1.3	2.6	3.6	1.3	3.8	1.3	4.0	
			0.8V	_	12.2	_	_	_	_	_	
			1.2V ± 0.1V	3.3	7.9	10.1	3.3	11.1	3.3	11.1	
	OΓ	Y	1.5V ± 0.1V	2.1	7.0	9.3	2.1	10.1	2.1	10.1	
t _{dis}	OE	Y	1.8V ± 0.15V	1.7	6.3	8.7	1.7	9.1	1.7	9.1	ns
		-	2.5V ± 0.2V	1.4	4.9	7.6	1.4	7.8	1.4	7.8	
			3.3V ± 0.3V	1.3	4.1	5.7	1.3	5.8	1.3	5.8	



Switching Characteristics (continued)

C_L=15pF, See Figure 1

B	From	То		T	A = +25°	С	T _A = -40 ℃	C to +85℃	T _A = -40 ℃	to +125℃	11
Parameter	Input	Output	V _{CC}	Min	Тур	Max	Min	Max	Min	Max	Unit
			V8.0	_	27.4	_	_	_	_	_	
			1.2V ± 0.1V	3.6	7.2	14.1	3.3	15.8	3.3	17.5]
	Α	Y	1.5V ± 0.1V	3.0	5.1	8.1	2.5	9.8	2.5	10.9]
t _{pd}	A	Ť	1.8V ± 0.15V	2.2	4.3	6.3	2.0	7.9	2.0	8.8	ns
			2.5V ± 0.2V	2.0	3.7	4.9	1.8	6.0	1.8	6.7	1
			3.3V ± 0.3V	2.0	3.5	4.4	1.8	5.4	1.8	6.1	1
	OE		0.8V	_	79.2	_	_	_	_	_	ns
		Y	1.2V ± 0.1V	3.6	7.8	15.8	3.3	17.1	3.3	17.1	
			1.5V ± 0.1V	3.0	5.4	8.8	2.9	9.4	2.9	9.7	
t _{en}			1.8V ± 0.15V	2.1	4.3	6.7	2.0	7.3	2.0	7.7	
			2.5V ± 0.2V	1.8	3.4	4.8	1.7	5.2	1.7	5.6	
			3.3V ± 0.3V	1.6	3.1	4.3	1.5	4.5	1.5	4.7	1
			V8.0	_	14.9	_	_	_	_	_	
			1.2V ± 0.1V	3.7	9.0	12.7	3.7	13.0	3.7	13.0]
	OE	Y	1.5V ± 0.1V	2.5	8.1	11.5	2.5	12.0	2.5	12.0]
t _{dis}	OE	ř	1.8V ± 0.15V	2.0	7.9	10.1	2.0	10.4	2.0	10.4	ns
		 	2.5V ± 0.2V	1.7	7.7	9.7	1.7	9.9	1.7	9.9	
			3.3V ± 0.3V	1.5	7.2	9.0	1.5	9.3	1.5	9.3]

C_L=30pF, See Figure 1

Dawamatan	From	То	v	Т	A = +25°	С	T _A = -40 °C	C to +85℃	T _A = -40 ℃	to +125℃	I Imia
Parameter	Input	Output	V _{CC}	Min	Тур	Max	Min	Max	Min	Max	Unit
			V8.0	_	37.4	_	_	_	_	_	
			1.2V ± 0.1V	4.8	9.5	18.7	4.4	21.4	4.4	24.0	
	Α	Y	1.5V ± 0.1V	4.0	6.7	10.8	3.0	13.0	3.0	14.5	
t _{pd}	A	Ť	1.8V ± 0.15V	2.5	5.6	8.4	2.5	10.3	2.5	11.5	ns
			2.5V ± 0.2V	2.2	4.8	6.3	2.2	7.8	2.2	8.7	
			3.3V ± 0.3V	2.0	4.6	5.8	2.0	7.0	2.0	8.3	
		Y	V8.0	_	90.6	_	_	_	_	_	ns
	OE		1.2V ± 0.1V	4.7	10.0	20.4	4.3	22.0	4.3	22.0	
			1.5V ± 0.1V	3.5	6.9	11.3	3.5	12.0	3.5	12.5	
t _{en}	OE		1.8V ± 0.15V	2.6	5.6	8.6	3.2	9.5	3.2	10.1	
			2.5V ± 0.2V	2.3	4.5	6.3	2.9	6.8	2.9	7.3	
			3.3V ± 0.3V	2.2	4.2	5.8	2.7	6.4	2.7	6.7	
			V8.0	_	51.6	_	_	_	_	_	
			1.2V ± 0.1V	4.7	12.8	15.0	4.7	15.5	4.7	15.5	
	OE	Y	1.5V ± 0.1V	3.0	11.8	13.5	3.0	13.9	3.0	13.9	no
t _{dis}	OE	ī	1.8V ± 0.15V	2.6	10.8	12.7	2.6	13.2	2.6	12.7	ns
			2.5V ± 0.2V	2.3	10.1	12.0	2.3	12.5	2.3	12.5	
			3.3V ± 0.3V	2.2	9.0	11.5	2.2	12.0	2.2	12.0	



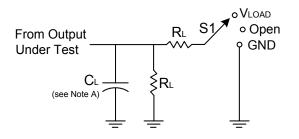
Operating and Package Characteristics (@T_A = +25 ℃, unless otherwise specified.)

	Parameter	Test Conditio	ns	Vcc	Тур	Unit
				0.8V	6.9	
				1.2V ± 0.1V	6.7	
	Power Dissipation	f = 1MH	lz	1.5V ± 0.1V	6.6	
C_{pd}	Capacitance	No Loa	d	1.8V ± 0.15V	6.5	pF
				2.5V ± 0.2V	6.4	
				3.3V ± 0.3V	6.3	
Ci	Input Capacitance	$V_i = V_{CC}$ or	GND	0V or 3.3V	1.5	pF
		SOT353		_	371	
		X2-DFN0808-4	(Note 9)	_	430	
0	Thermal Resistance	X1-DFN1010-6		_	435	00.004
θ_{JA}	Junction-to-Ambient	X2-DFN1010-6		_	445	- °C/W
		X2-DFN1409-6		_	470	
		X2-DFN1410-6		_	460	
		SOT353		_	143	
		X2-DFN0808-4		_	240	
0	Thermal Resistance	X1-DFN1010-6	(NI-+- O)	_	250	00.444
θ_{JC}	Junction-to-Case	X2-DFN1010-6	(Note 9)	_	250	- °C/W
		X2-DFN1409-6		_	275	
		X2-DFN1410-6		_	265	

Note: 9. Test condition for each of the six package types: Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.

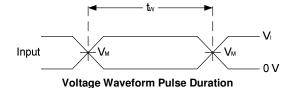


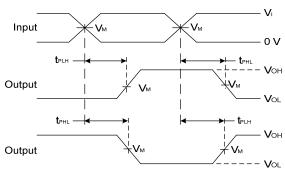
Parameter Measurement Information



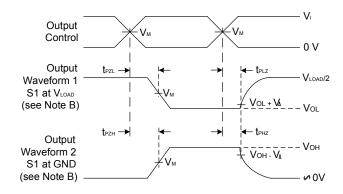
TEST	S1	R_L
tplH/tpHL	Open	1ΜΩ
t _{PLZ} /t _{PZL}	Vload	5kΩ
t _{PHZ} /t _{PZH}	GND	5kΩ

V	In	puts	V	V _{LOAD}	CL	V Δ
V _{CC}	VI	t _r /t _f	V _M			
0.8V	V _{CC}	≤3ns	V _{CC} /2	2 X V _{CC}	5, 10, 15, 30pF	0.1V
1.2V ± 0.1V	V _{CC}	≤3ns	V _{CC} /2	2 X V _{CC}	5, 10, 15, 30pF	0.1V
1.5V ± 0.1V	V _{CC}	≤3ns	V _{CC} /2	2 X V _{CC}	5, 10, 15, 30pF	0.1V
1.8V ± 0.15V	V_{CC}	≤3ns	V _{CC} /2	2 X V _{CC}	5, 10, 15, 30pF	0.15V
2.5V ± 0.2V	V _{CC}	≤3ns	V _{CC} /2	2 X V _{CC}	5, 10, 15, 30pF	0.15V
3.3V ± 0.3V	V _{CC}	≤3ns	V _{CC} /2	2 X V _{CC}	5, 10, 15, 30pF	0.3V





Voltage Waveform Propagation Delay Times Inverting and Non Inverting Outputs



Voltage Waveform Enable and Disable Times Low and High Level Enabling

March 2015

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Figure 1 Load Circuit and Voltage Waveforms

Notes: A. Includes test lead and test apparatus capacitance.

B. All pulses are supplied at pulse repetition rate ≤ 10MHz.

C. Inputs are measured separately one transition per measurement.

D. t_{PLZ} and t_{PHZ} are the same as t_{dis.}

E. t_{PZL} and t_{PZH} are the same as t_{EN}.

F. t_{PLH} and t_{PHL} are the same as $t_{PD.}$



Marking Information

(1) SOT353

(Top View)

XX Y WX

2

XX: Identification code

Y: Year 0~9

 \underline{W} : Week : A $^{\sim}$ Z : 1 $^{\sim}$ 26 week;

a~z: 27~52 week; z represents 52 and 53 week

X: A~Z: Internal code

Part Number	Package	Identification Code
74AUP1G126SE-7	SOT353	XZ

(2) X2-DFN0808-4, X2-DFN1010-6 X2-DFN1409-6 and X2-DFN1410-6

(Top View)

XX $\underline{Y}\underline{W}\underline{X}$ XX: Identification Code

Y: Year: 0~9

 \overline{W} : Week : A~Z : 1~26 week;

a~z: 27~52 week; z represents 52 and 53 week

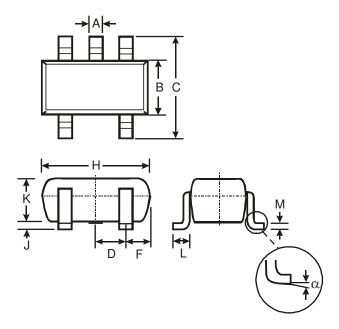
X: A~Z: Internal code

Part Number	Package	Identification Code
74AUP1G126FS3-7	X2-DFN0808-4	YZ
74AUP1G126FW5-7	X1-DFN1010-6	QY
74AUP1G126FW4-7	X2-DFN1010-6	XZ
74AUP1G126FX4-7	X2-DFN1409-6	HR
74AUP1G126FZ4-7	X2-DFN1410-6	XZ

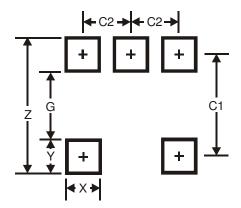


SOT353 Package Outline Dimensions and Suggested Pad Layout

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



	SOT353				
Dim	Min	Max	Тур		
Α	0.10	0.30	0.25		
В	1.15	1.35	1.30		
С	2.00	2.20	2.10		
D		0.65 Typ	כ		
F	0.40	0.45	0.425		
Η	1.80	2.20	2.15		
J	0	0.10	0.05		
K	0.90	1.00	1.00		
L	0.25	0.40	0.30		
М	0.10	0.22	0.11		
α	0°	8°	-		
All Dimensions in mm					

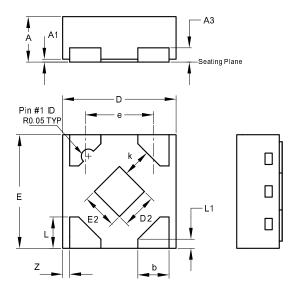


Dimensions	Value (in mm)
Z	2.5
G	1.3
Х	0.42
Υ	0.6
C1	1.9
C2	0.65

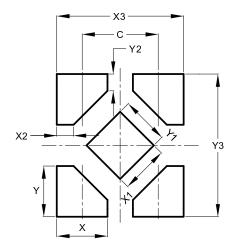


X2-DFN0808-4 Package Outline Dimensions and Suggested Pad Layout

 $Please see AP02002 \ at \ http://www.diodes.com/datasheets/ap02002.pdf \ for \ the \ latest \ version.$



	X2-DFN0808-4				
Dim	Min	Max	Тур		
Α	0.25	0.35	0.30		
A1	0	0.04	0.02		
A3	-	-	0.13		
b	0.17	0.27	0.22		
D	0.75	0.85	0.80		
D2	0.15	0.35	0.25		
E	0.75	0.85	0.80		
E2	0.15	0.35	0.25		
е	-	-	0.48		
k	0.20	-	-		
L	0.17	0.27	0.22		
L1	0.02	0.12	0.07		
Z	-	-	0.05		
All Dimensions in mm					

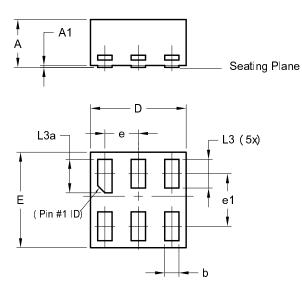


Dimensions	Value
С	0.480
X	0.320
X1	0.300
X2	0.106
Х3	0.800
Υ	0.320
Y1	0.300
Y2	0.106
Y3	0.900

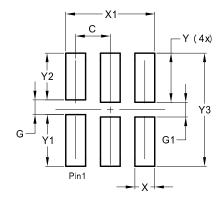


X1-DFN1010-6 (Type B) Package Outline Dimensions and Suggested Pad Layout

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



	X1-DFN1010-6				
	(Ty	pe B)			
Dim	Min	Max	Тур		
Α	-	0.50	0.39		
A1	-	0.04	-		
b	0.12	0.20	0.15		
D	0.95	1.050	1.00		
Е	0.95	1.050	1.00		
е	e 0.35 BSC				
e1		0.55 BSC			
L3	0.27	0.30	0.30		
L3a	0.32	0.40	0.35		
All Dimensions in mm					

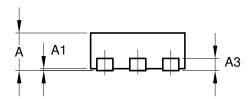


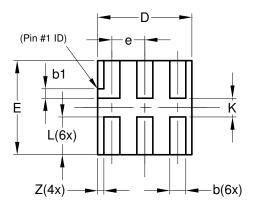
Dimensions	Value (in mm)
С	0.350
G	0.150
G1	0.150
Х	0.200
X1	0.900
Υ	0.500
Y1	0.525
Y2	0.475
Y3	1.150



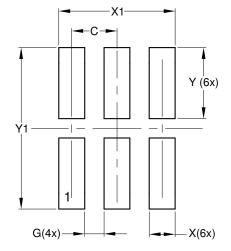
X2-DFN1010-6 Package Outline Dimensions and Suggested Pad Layout

 $Please see AP02002 \ at \ http://www.diodes.com/datasheets/ap02002.pdf \ for \ the \ latest \ version.$





)	X2-DFN1010-6				
Dim	Min	Max	Тур		
Α		0.40	0.39		
A 1	0.00	0.05	0.02		
A3		_	0.13		
b	0.14	0.20	0.17		
b1	0.05	0.15	0.10		
D	0.95	1.05	1.00		
E	0.95	1.05	1.00		
е		_	0.35		
L	0.35	0.45	0.40		
K	0.15	_			
Z		_	0.065		
All Dimensions in mm					

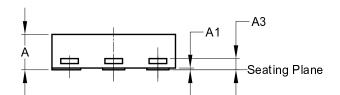


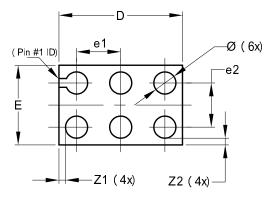
Dimensions	Value (in mm)
С	0.350
G	0.150
Х	0.200
X1	0.900
Υ	0.550
Y1	1.250



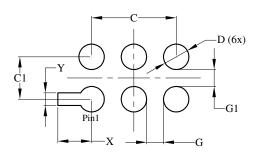
X2-DFN1409-6 Package Outline Dimensions and Suggested Pad Layout

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.





X2-DFN1409-6				
Dim	Min	Max	Тур	
Α	-	0.40	0.39	
A1	0	0.05	0.02	
A3	-	-	0.13	
Ø	0.20	0.30	0.25	
D	1.35	1.45	1.40	
Е	0.85	0.95	0.90	
e1	-	-	0.50	
e2	-	1	0.50	
Z 1	-	-	0.075	
Z2	-	-	0.075	
All Dimensions in mm				

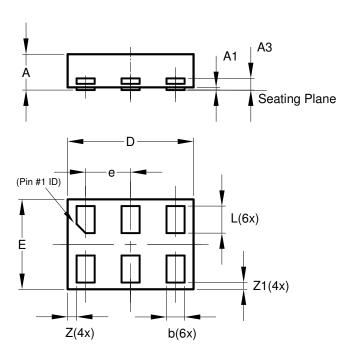


Dimensions	Value (in mm)	
С	1.000	
C1	0.500	
D	0.300	
G	0.200	
G1	0.200	
Х	0.400	
Y	0.150	

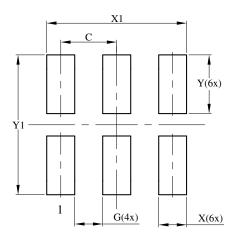


X2-DFN1410-6 Package Outline Dimensions and Suggested Pad Layout

 $Please see AP02002 \ at \ http://www.diodes.com/datasheets/ap02002.pdf \ for \ the \ latest \ version.$



X2-DFN1410-6				
Dim	Min	Max	Тур	
Α	_	0.40	0.39	
A 1	0.00	0.05	0.02	
A3			0.13	
b	0.15	0.25	0.20	
D	1.35	1.45	1.40	
Е	0.95	1.05	1.00	
e	_		0.50	
L	0.25	0.35	0.30	
Z			0.10	
Z 1	0.045	0.105	0.075	
All Dimensions in mm				



Dimensions	Value	
Difficitions	(in mm)	
С	0.500	
G	0.250	
X	0.250	
X1	1.250	
Υ	0.525	
Y1	1.250	



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NL17SG32P5T5G NL17SG86DFT2G NLU1G32CMUTCG NLV14001UBDR2G NLVVHC1G132DTT1G NLVVHC1G86DTT1G
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74LVC08ADTR2G MC74HCT20ADTR2G NLU1G08CMX1TCG NLV14093BDTR2G NLV17SZ00DFT2G NLV17SZ02DFT2G
NLV17SZ126DFT2G NLV27WZ17DFT2G NLV74HC02ADR2G NLV74HC08ADR2G NLVVHC1GT32DFT1G 74HC32S14-13 74LS133
74LVC1G32Z-7 M38510/30402BDA 74LVC1G86Z-7 74LVC2G08RA3-7 M38510/06202BFA NLV74HC08ADTR2G
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